

DOCKET NO.: 205973US99



#14/Ext 01
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7/12/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Kurt Eisenbeiser et al. : Group Art Unit: 2826

Application No.: 09/584,601

Filed: 31 May 2000

Examiner: S. Wilson

For: SEMICONDUCTOR DEVICE AND METHOD

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AMENDMENT

Honorable Commissioner of Patents and Trademarks,
Washington, D.C. 20231

SIR:

In response to the First Office Action dated 3 January 2001, please amend the above identified application as follows:

IN THE SPECIFICATION

On page 1, line 1, change the title to "FET WITH AMORPHOUS GATE INSULATION LAYER--.

On page 12, line 1, change the title to "FET WITH AMORPHOUS GATE INSULATION LAYER--.

IN THE CLAIMS

Substitute amended claims 1 and 9, all as shown immediately hereafter, for the respective claims previously existing in this application.

CLEAN VERSION OF AMENDED CLAIMS

Please enter new claim 1, as shown immediately hereafter.

1. A semiconductor device, comprising:
- a semiconductor substrate; and
 - a dielectric layer formed over the semiconductor substrate and having a first portion formed with an amorphous material and a second portion formed with a monocrystalline